

View Online at <https://aerobasegroup.com/nsn/5961-01-271-1762>

Inclosure Material:

Glass all semiconductor device diode

Overall Length:

0.170 inches all semiconductor device diode

Terminal Length:

1.000 inches all semiconductor device diode

Overall Diameter:

0.076 inches all semiconductor device diode

Internal Configuration:

Junction contact all semiconductor device diode

Internal Junction Configuration:

Pn all semiconductor device diode

Component Function Relationship:

Matched

Component Name And Quantity:

2 semiconductor device diode

Mounting Method:

Terminal all semiconductor device diode

Field Force Effect Type:

Electrostatic charge

Features Provided:

Hermetically sealed case and electrostatic sensitive

Semiconductor Material:

Silicon all semiconductor device diode

Voltage Rating In Volts Per Characteristic:

0.4 forward voltage, dc all semiconductor device diode

Current Rating Per Characteristic:

1.00 microamperes source cutoff current preset all semiconductor device diode

Power Rating Per Characteristic:

250.0 milliwatts small-signal input power, common-collector preset all semiconductor device diode

Maximum Operating Temperature Per Measurement Point:

125.0 degrees celsius junction all semiconductor device diode

Terminal Type And Quantity:

4 uninsulated wire lead all semiconductor device diode

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

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